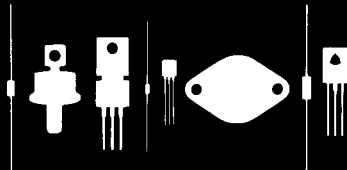


Central  
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145 Adams Avenue  
Hauppauge, New York 11788



PN4916  
PN4917

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE (EBC)

## DESCRIPTION

The CENTRAL SEMICONDUCTOR PN4916, PN4917 series types are epoxy molded silicon PNP small signal transistors manufactured by the epitaxial planar process for general purpose amplifier and switching applications.

## MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	VCBO	30	V
Collector-Emitter Voltage	VCEO	30	V
Emitter-Base Voltage	VEBO	5.0	V
Collector Current	IC	100	mA
Power Dissipation	PD	625	mW
Power Dissipation (TC=25°C)	PD	1.5	W
Operating and Storage Junction Temperature	TJ, TSTG	-65 TO +150	°C

## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	PN4916		PN4917		UNIT
		MIN	MAX	MIN	MAX	
ICES	VCE=15V		25		25	nA
ICES	VCE=15V, TA=65°C		25		25	µA
BVCBO	IC=10µA	30		30		V
BVCES	IC=10µA	30		30		V
BVCEO	IC=10mA	30		30		V
BVEBO	IE=10µA	5.0		5.0		V
VCE(SAT)	IC=1.0mA, IB=0.1mA		0.13		0.13	V
VCE(SAT)	IC=10mA, IB=1.0mA		0.14		0.14	V
VCE(SAT)	IC=50mA, IB=5.0mA		0.3		0.3	V
VBE(SAT)	IC=1.0mA, IB=0.1mA		0.75		0.75	V
VBE(SAT)	IC=10mA, IB=1.0mA	0.7	0.9	0.7	0.9	V
VBE(SAT)	IC=50mA, IB=5.0mA	0.75	1.1	0.75	1.1	V
hFE	VCE=1.0V, IC=100µA	40	-	100	-	
hFE	VCE=1.0V, IC=1.0mA	60	-	150	-	
hFE	VCE=1.0V, IC=10mA	70	200	150	300	
hFE	VCE=1.0V, IC=50mA	15	-	30	-	
fT	VCE=20V, IC=10mA, f=100MHz	400		450		MHz
Cob	VCE=10V, IE=0,		4.5		4.5	pF
Cib	VEB=0.5V, IC=0,		8.0		8.0	pF
ton	IC=50mA, IB1=5.0mA		40		40	ns
t <sub>off</sub>	IC=50mA, IB1=5.0mA, IB2=5.0mA		150		150	ns
tr <sub>b<sup>+</sup>c<sub>c</sub></sub>	VCE=20V, IC=10mA, f=80MHz		50		50	ps
NF	VCE=5.0V, IC=1.0mA, RS=100Ω, BW=15MHz, f=100MHz		6.0		6.0	dB
NF	VCE=5.0V, IC=100µA, RS=1.0kΩ, BW=15.7kHz, 3.0 dB Points @ 10Hz and 10kHz		4.0		4.0	dB

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